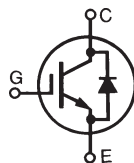


High Voltage XPT™ IGBT w/ Diode

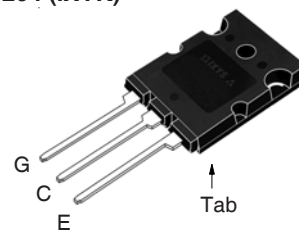
IXYK30N170CV1
IXYX30N170CV1



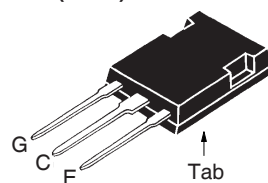
$$\begin{aligned} V_{CES} &= 1700V \\ I_{C110} &= 30A \\ V_{CE(sat)} &\leq 4.0V \\ t_{fi(typ)} &= 95ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 175°C	1700	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 175°C , $R_{GE} = 1M\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	100	A
I_{C110}	$T_C = 110^\circ\text{C}$	30	A
I_{F110}	$T_C = 110^\circ\text{C}$	38	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1ms	250	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ\text{C}$, $R_G = 2.7\Omega$ Clamped Inductive Load	$I_{CM} = 120$ 1360	A V
P_C	$T_C = 25^\circ\text{C}$	937	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
M_d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in
F_C	Mounting Force (PLUS247)	20..120 / 4.5..27	N/lb
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXYK)



PLUS247 (IXYX)



G = Gate D = Collector
S = Emitter Tab = Collector

Features

- International Standard Packages
- High Voltage Package
- High Blocking Voltage
- Low Saturation Voltage

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu\text{A}$, $V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 250\mu\text{A}$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			25 μA 4 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 30A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ\text{C}$		3.5 4.6	V V

Symbol Test Conditions
 $(T_J = 25^\circ\text{C Unless Otherwise Specified})$
Characteristic Values
Min. Typ. Max.

g_{fs}	$I_C = 30\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	17	28	S
R_{Gi}	Gate Input Resistance		2.8	Ω
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3100	pF
C_{oes}			210	pF
C_{res}			55	pF
$Q_{g(on)}$	$I_C = 30\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		150	nC
Q_{ge}			15	nC
Q_{gc}			65	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 2.7\Omega$ Note 2		16	ns
t_{ri}			33	ns
E_{on}			3.6	mJ
$t_{d(off)}$			143	ns
t_{fi}			95	ns
E_{off}			1.8	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 30\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 2.7\Omega$ Note 2		16	ns
t_{ri}			33	ns
E_{on}			5.5	mJ
$t_{d(off)}$			193	ns
t_{fi}			134	ns
E_{off}			3.5	mJ
R_{thJC}			0.16	$^\circ\text{C/W}$
R_{thCS}			0.15	$^\circ\text{C/W}$

Reverse Diode (FRED)
 $(T_J = 25^\circ\text{C}, \text{ Unless Otherwise Specified})$

Symbol	Test Conditions	Characteristic Value	Min.	Typ.	Max.
V_F	$I_F = 30\text{A}, V_{GE} = 0\text{V}, \text{Note 1}$ $T_J = 150^\circ\text{C}$			3.7	3.5 V
I_{RM}	$I_F = 30\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 500\text{A}/\mu\text{s},$ $V_R = 1200\text{V}, T_J = 150^\circ\text{C}$			32	A
t_{rr}				175	ns
R_{thJC}					0.36 $^\circ\text{C/W}$

Notes:

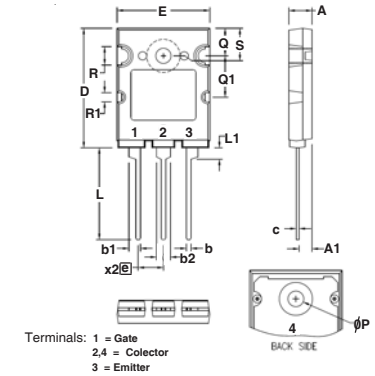
1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

PRELIMINARY TECHNICAL INFORMATION

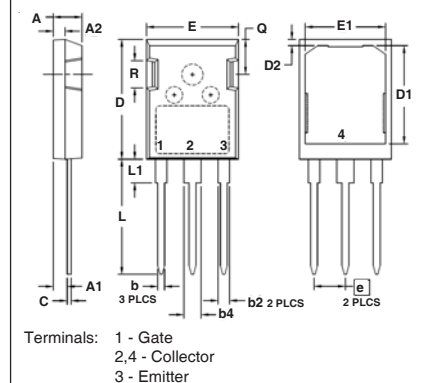
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,592 4,931,844 5,049,961 5,237,481 6,162,665 6,404,065 B1 6,683,344 6,727,585 7,005,734 B2 7,157,338B2
 by one or more of the following U.S. patents: 4,860,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692 7,063,975 B2
 4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2 7,071,537

TO-264 Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.30
A1	.102	.118	2.60	3.00
b	.035	.049	0.90	1.25
b1	.091	.106	2.30	2.70
b2	.110	.126	2.80	3.20
c	.020	.033	0.50	0.85
D	1.012	1.035	25.70	26.30
E	.776	.799	19.70	20.30
e	.215 BSC		5.46 BSC	
L	.768	.807	19.50	20.50
L1	.091	.106	2.30	2.70
ϕP	.122	.138	3.10	3.50
Q	.228	.244	5.80	6.20
Q1	.346	.362	8.80	9.20
ϕR	.150	.165	3.80	4.20
$\phi R1$	.071	.087	1.80	2.20
S	.228	.244	5.80	6.20

PLUS 247™ Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.520	.560	13.08	14.22
e	.215 BSC		5.45 BSC	
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83

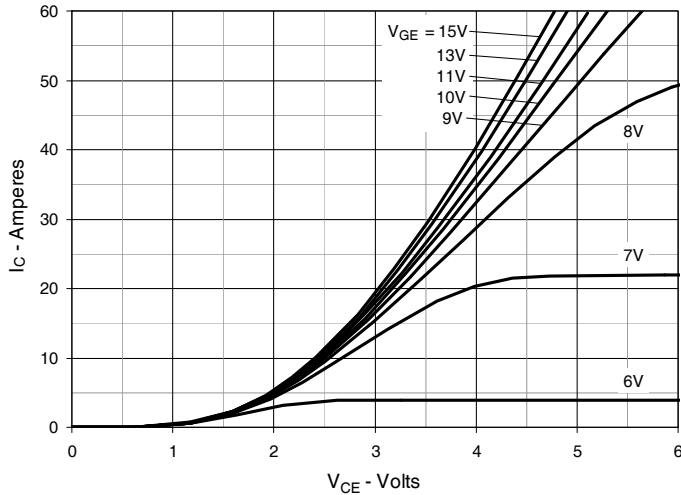
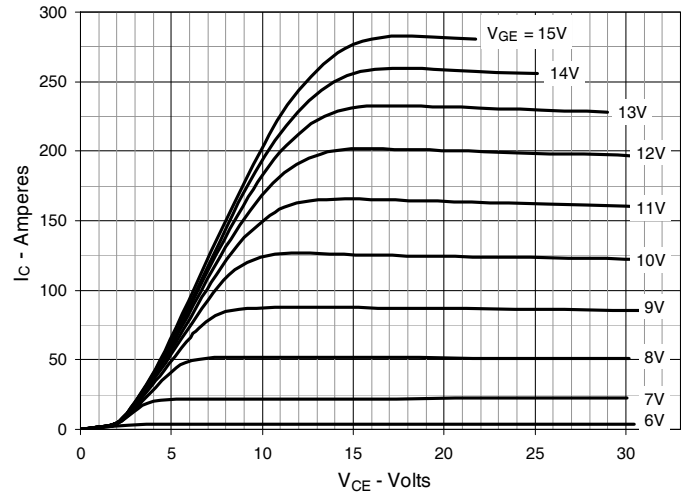
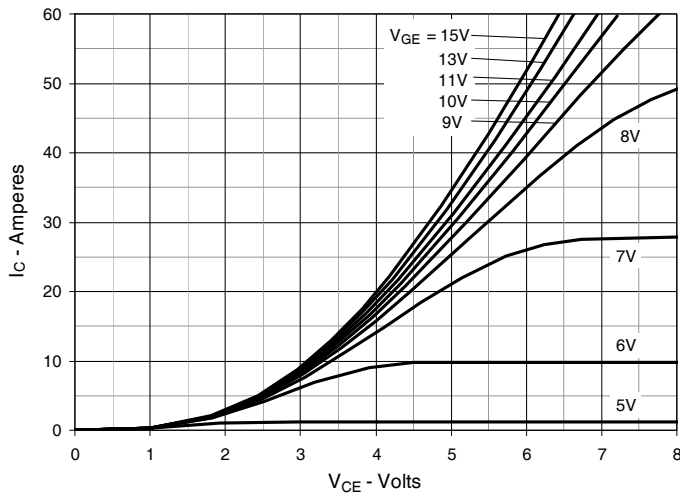
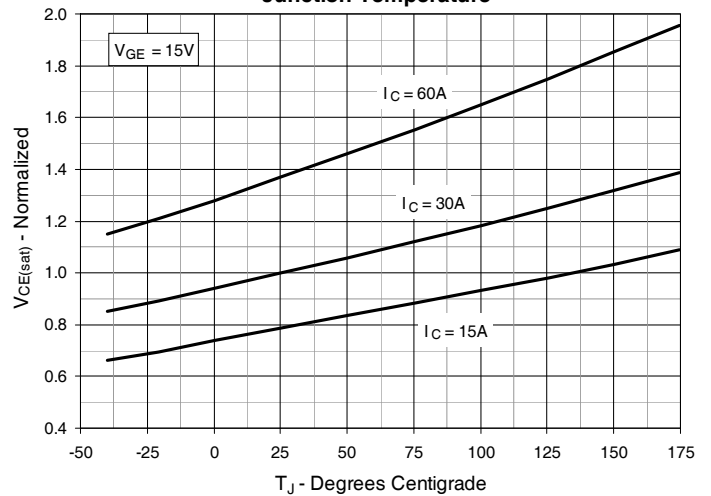
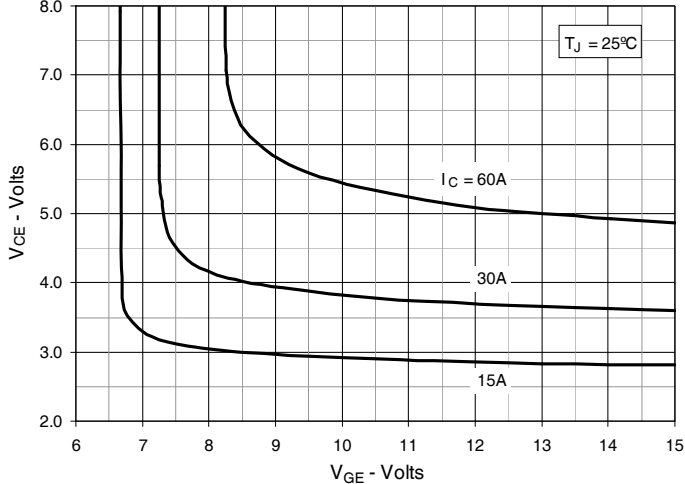
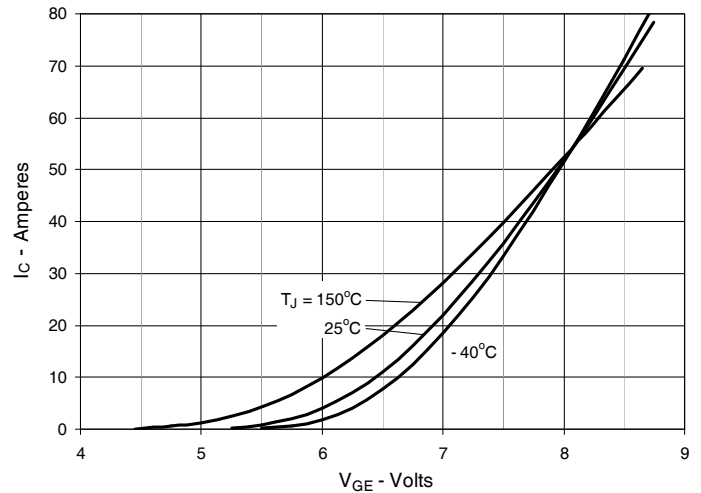
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


Fig. 7. Transconductance

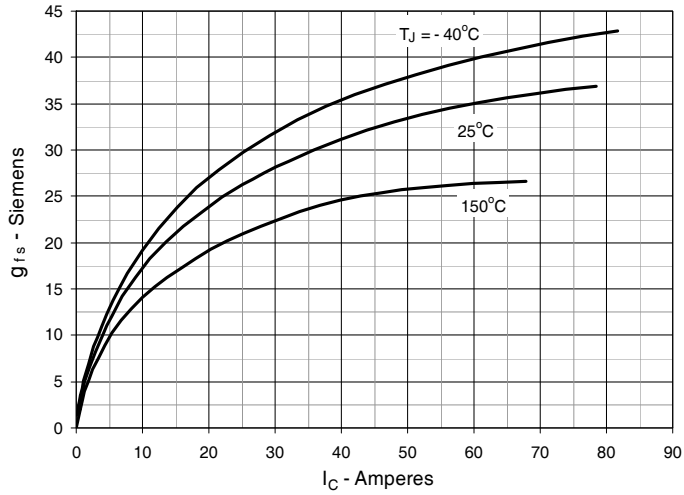


Fig. 8. Gate Charge

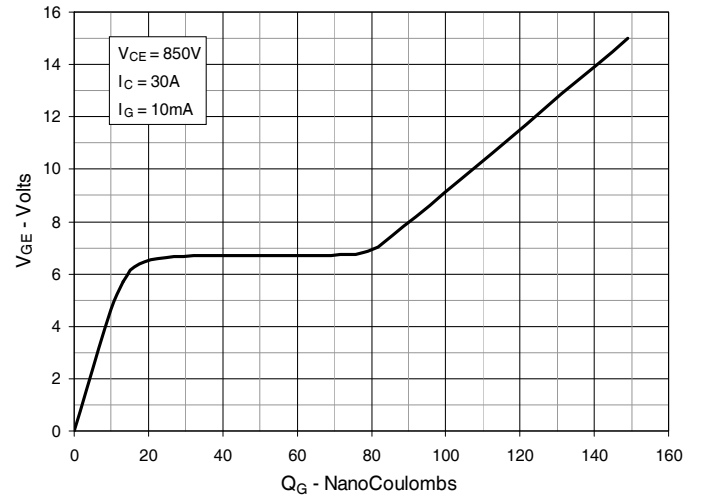


Fig. 9. Capacitance

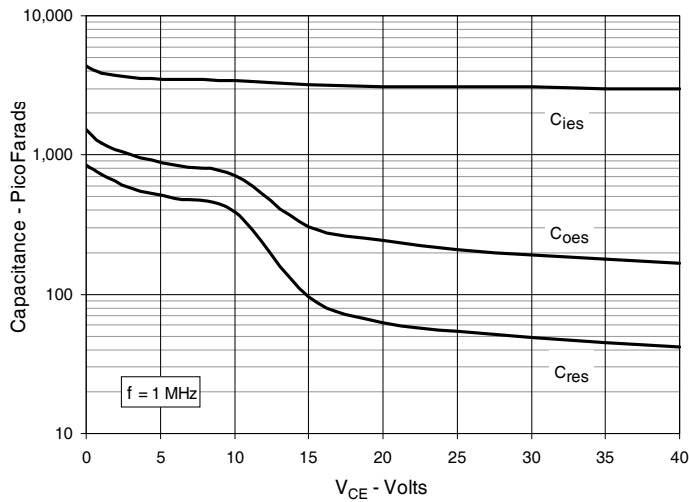


Fig. 10. Reverse-Bias Safe Operating Area

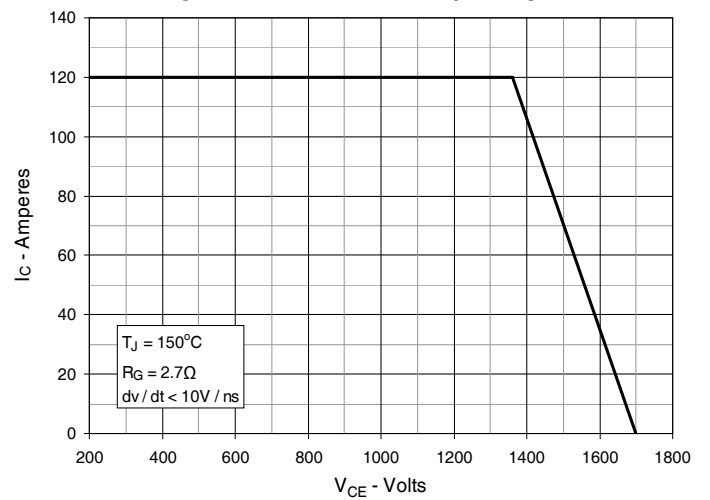


Fig. 11. Maximum Transient Thermal Impedance (IGBT)

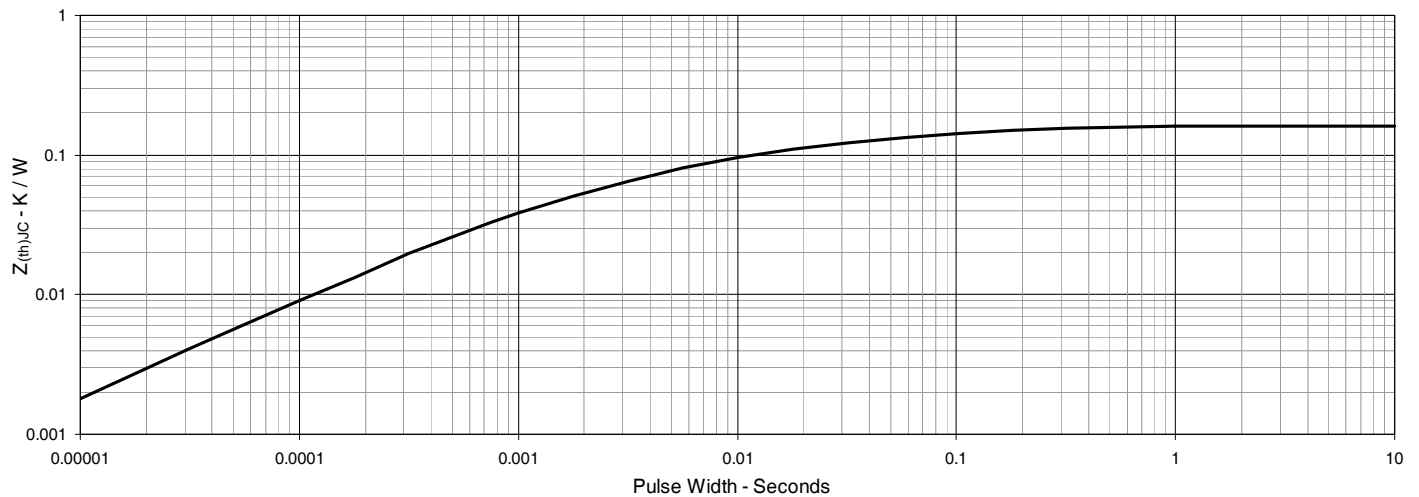


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

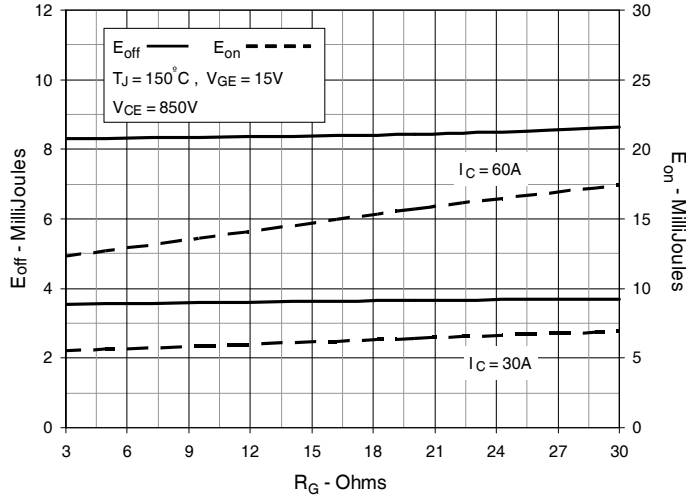


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

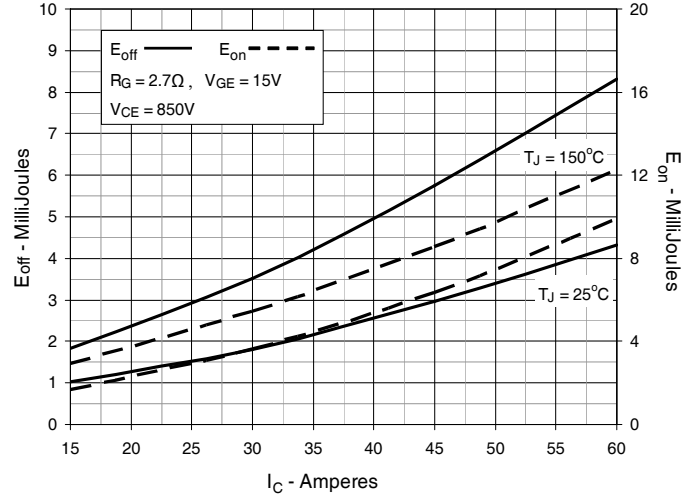


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

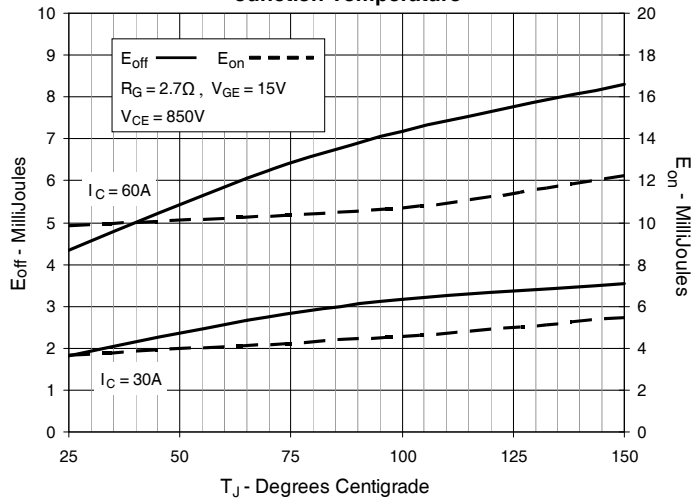


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

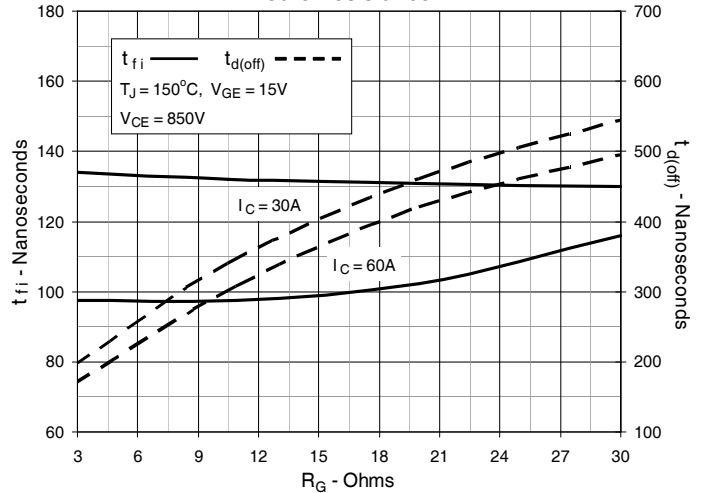


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

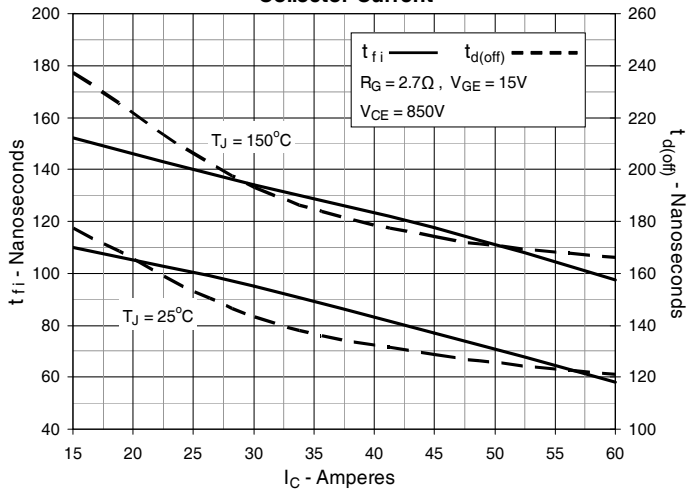


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

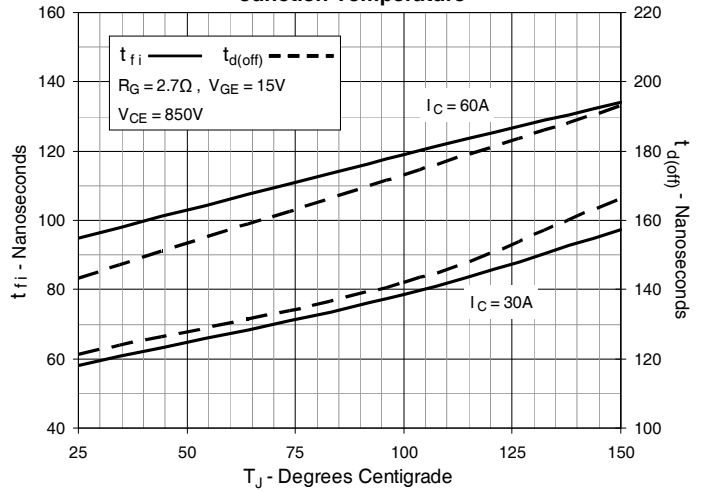


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

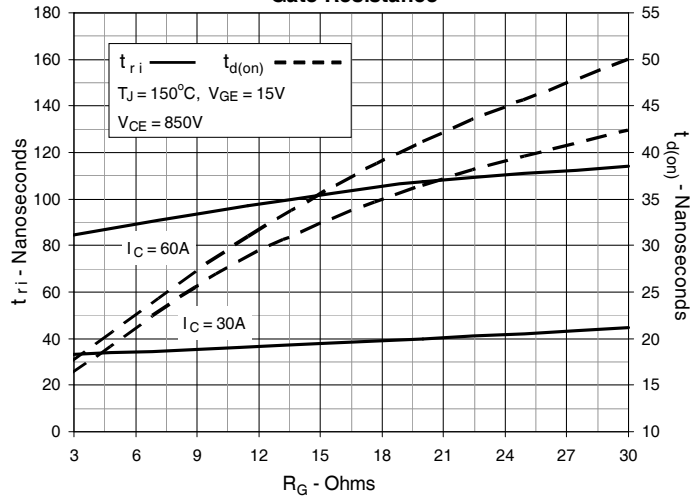


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

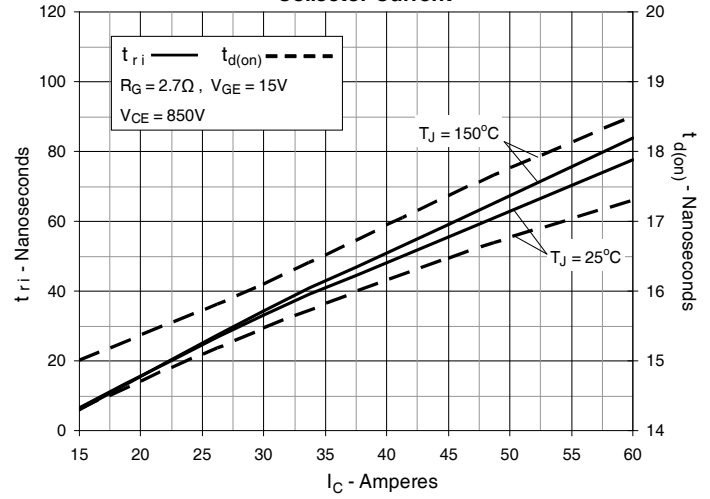


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

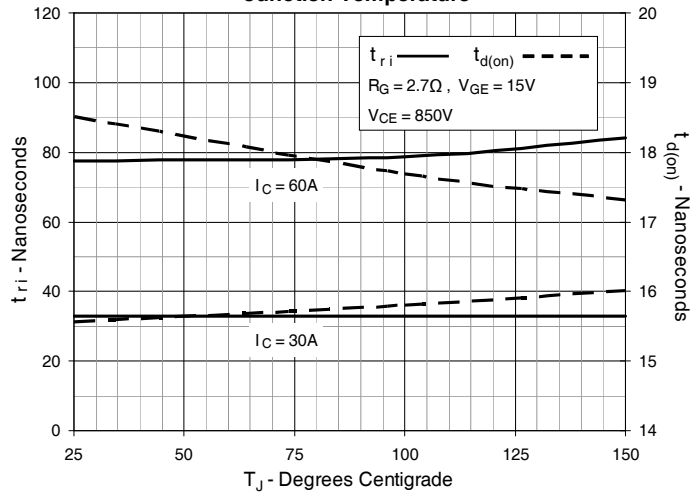
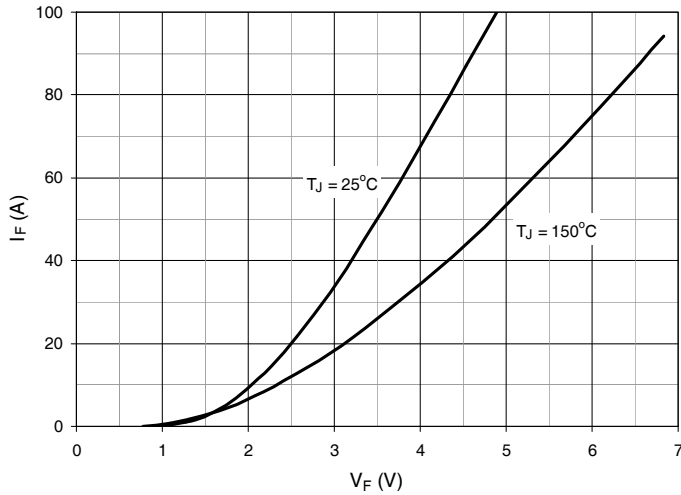
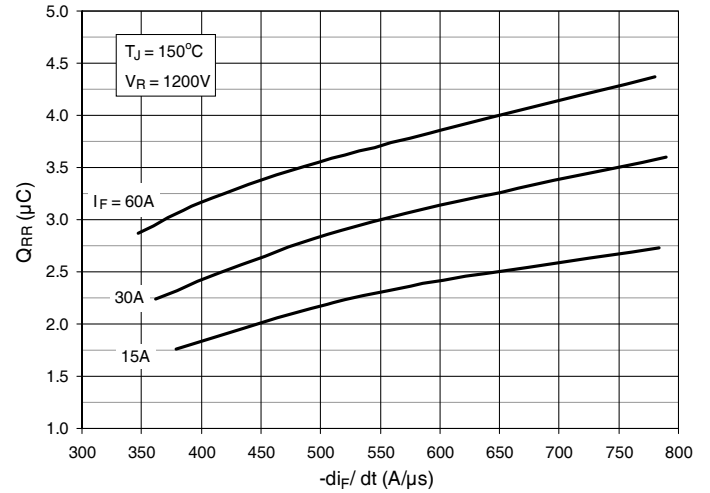
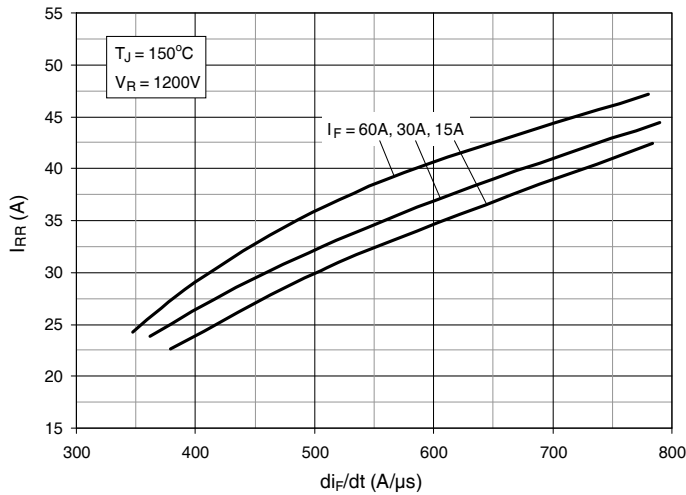
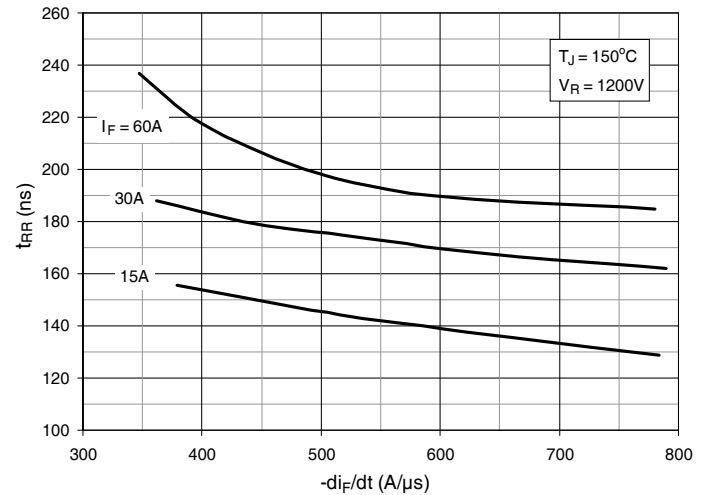
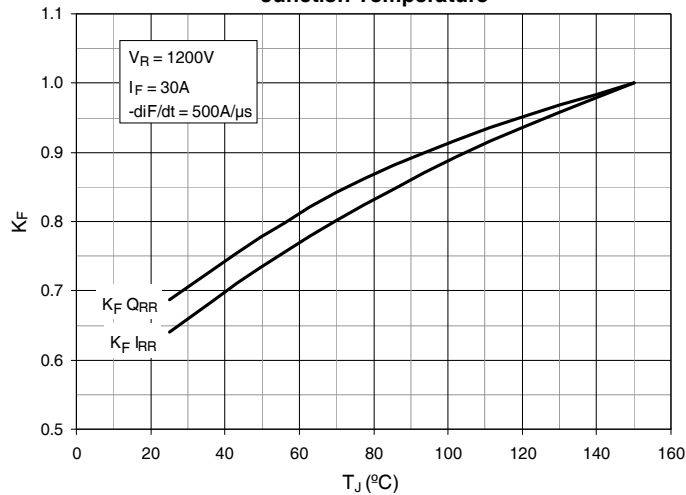
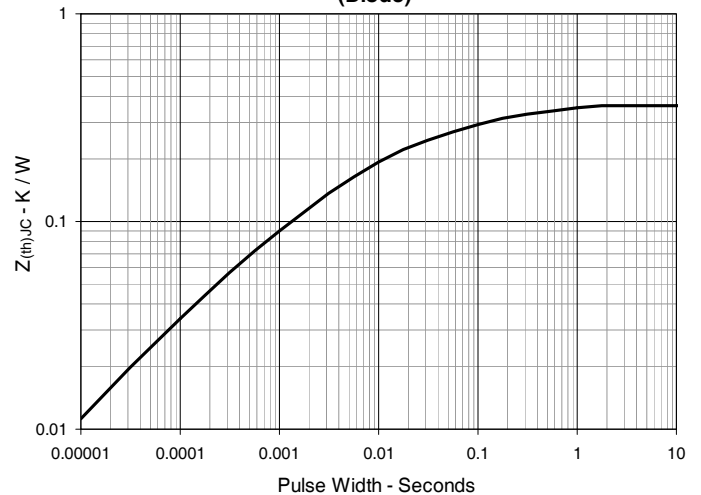


Fig. 21. Diode Forward Characteristics

Fig. 22. Reverse Recovery Charge vs. $-di_F/dt$

Fig. 23. Reverse Recovery Current vs. $-di_F/dt$

Fig. 24. Reverse Recovery Time vs. $-di_F/dt$

Fig. 25. Dynamic Parameters Q_{RR} , I_{RR} vs. Junction Temperature

Fig. 26. Maximum Transient Thermal Impedance (Diode)




Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.